NL17SG34

Single Buffer

The NL17SG34 MiniGate[™] is an advanced high-speed CMOS Buffer in ultra-small footprint.

The NL17SG34 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: t_{PD} = 2.3 ns (Typ) at V_{CC} = 3.0 V, C_L = 15 pF
- Low Power Dissipation: $I_{CC} = 0.5 \ \mu A \ (Max)$ at $T_A = 25^{\circ}C$
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- These are Pb-Free and Halide-Free Devices

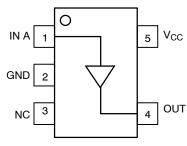


Figure 1. SOT-953 (Top Thru View)

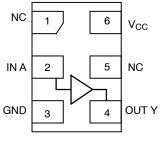
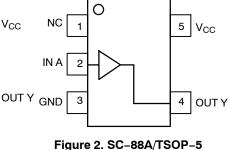


Figure 3. UDFN (Top View)



(Top View)

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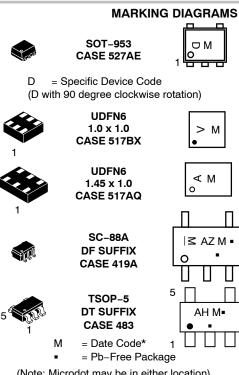
Figure 4. Logic Symbol

IN A



ON Semiconductor®

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(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT						
SOT-953 SC88A/TSOP5 UDFN6						
1	IN A	NC	NC			
2	GND	IN A	IN A			
3	NC	GND	GND			
4 OUT Y OUT Y OUT Y						
5 V _{CC} V _{CC} NC						
6			V _{CC}			

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

ORDERING INFORMATION

OUT Y

See detailed ordering and shipping information on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +5.5	V
V _{IN}	DC Input Voltage		-0.5 to +4.6	V
V _{OUT}	DC Output Voltage	Output at High or Low State Power–Down Mode ($V_{CC} = 0 V$)	-0.5 to V _{CC} +0.5 -0.5 to +4.6	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC}	DC Supply Current per Supply Pin		±20	mA
I _{GND}	DC Ground Current per Ground Pin		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
ILATCHUP	Latchup Performance Above V _{CC} a	and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
Tested to EIA/JESD22-A114-A.
Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low Stat Power-Down Mode (V _{CC} = 0 \	e 0.0 /) 0.0	V _{CC} 3.6	V
T _A	Operating Temperature Range	-55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fail Rate $$V_{CC}$$ = 3.3 V \pm 0.3	V 0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

				T _A = 2		25°C		T _A = −55°C to +125°C	
Symbol	Parameter	C	onditions	V _{CC} (V)	Min	Max	Min	Max	Unit
VIH	High-Level Input			0.9	V _{CC}		V _{CC}		V
	Voltage			1.1 to 1.3	0.7xV _{CC}		0.7xV _{CC}		
				1.4 to 1.6	0.65xV _{CC}		$0.65 \mathrm{xV}_{\mathrm{CC}}$		
				1.65 to 1.95	0.65xV _{CC}		$0.65 \mathrm{xV}_{\mathrm{CC}}$		
				2.3 to 2.7	1.7		1.7		
				3.0 to 3.6	2.0		2.0		
V _{IL}	Low-Level Input			0.9		GND		GND	V
	Voltage			1.1 to 1.3		0.3xV _{CC}		0.3xV _{CC}	
				1.4 to 1.6		0.35xV _{CC}		0.35xV _{CC}	
				1.65 to 1.95		0.35xV _{CC}		0.35xV _{CC}	
				2.3 to 2.7		0.7		0.7	
				3.0 to 3.6		0.8		0.8	
V _{OH}	High–Level	V _{IN} =	I _{OH} = -20 μA	0.9	0.75		0.75		V
	Output Voltage	V _{IH} or V _{IL}	I _{OH} = -0.3 mA	1.1 to 1.3	0.75xV _{CC}		0.75xV _{CC}		
			I _{OH} = -1.7 mA	1.4 to 1.6	0.75xV _{CC}		0.75xV _{CC}		
			I _{OH} = -3.0 mA	1.65 to 1.95	Vcc-0.45		Vcc-0.45		
			I _{OH} = -4.0 mA	2.3 to 2.7	2.0		2.0		
			I _{OH} = -8.0 mA	3.0 to 3.6	2.48		2.48		
V _{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9		0.1		0.1	V
	Output Voltage	V _{IH} or V _{IL}	I _{OL} = 0.3 mA	1.1 to 1.3		$0.25 \text{xV}_{\text{CC}}$		$0.25 \mathrm{xV}_{\mathrm{CC}}$	
			I _{OL} = 1.7 mA	1.4 to 1.6		$0.25 \text{xV}_{\text{CC}}$		$0.25 \mathrm{xV}_{\mathrm{CC}}$	
			I _{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	
			I _{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	1
			I _{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	1
I _{IN}	Input Leakage Current	0 ≤	$V_{IN} \leq 3.6 V$	0 to 3.6		±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} =	V _{CC} or GND	3.6		0.5		10.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

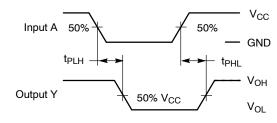
NL17SG34

Symbol	Parameter	Parameter Test Condition V_{CC} (V) $T_A = 25^{\circ} C$)		_ = ⊳ +125°C			
				Min	Тур	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	$C_L = 10 \text{ pF},$	0.9	-	12.6	15.3	-	19.0	ns
t _{PHL}	A to Y	$R_L = 1 M\Omega$	1.1 to 1.3	-	8.7	13.4	-	15.2	
			1.4 to 1.6	-	4.9	8.5	-	10.0	
			1.65 to 1.95	-	3.8	6.2	-	6.7	
			2.3 to 2.7	-	2.6	3.9	-	4.4	
			3.0 to 3.6	-	2.1	3.1	-	3.7	
		$C_L = 15 \text{ pF},$	0.9	-	13.0	16.6	-	20.8	ns
		$R_{L} = 1 M\Omega$	1.1 to 1.3	-	8.0	12.5	-	15.7	
			1.4 to 1.6	-	5.4	9.3	-	11.2	
			1.65 to 1.95	-	4.2	6.9	-	7.1	
			2.3 to 2.7	-	2.8	4.4	-	5.0	
			3.0 to 3.6	-	2.3	3.4	-	3.9	
		$C_L = 30 \text{ pF},$	0.9	-	14.5	17.6	-	22.4	ns
		$\overline{R_L} = 1 M\Omega$	1.1 to 1.3	-	9.5	13.5	-	18.8	
			1.4 to 1.6	-	7.4	11.1	-	15.9	
			1.65 to 1.95	-	5.6	9.2	-	9.6	
			2.3 to 2.7	-	3.7	5.7	-	6.1	1
			3.0 to 3.6	-	2.9	4.4	-	4.8	1
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	-	-	pF

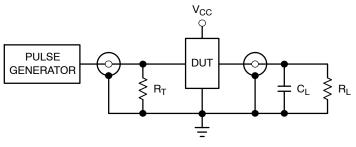
AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NL17SG34







 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
NL17SG34P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel
NL17SG34DFT2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NL17SG34DTT1G*	TSOP–5 (Pb–Free)	3000 / Tape & Reel
NL17SG34AMUTCG*	UDFN6 1.45x1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG34CMUTCG*	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*In Development

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DATE 11 APR 2023

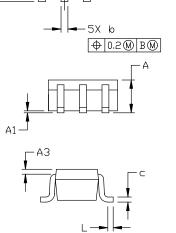


SCALE 2:1

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

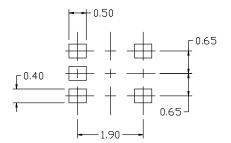
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



e

F1



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our
 Pb-Free strategy and soldering details,
 please download the DN Semiconductor
 Soldering and Mounting Techniques
 Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS			
ויונע	MIN.	NDM.	MAX,	
А	0.80	0.95	1.10	
A1			0.10	
A3		0.20 REF		
b	0.10	0.20	0.30	
C	0.10		0,25	
D	1.80	2.00	5.20	
E	2.00	2.10	5.20	
E1	1.15	1.25	1.35	
e		0.65 BSI	C	
L	0.10	0.15	0.30	

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

PIN 1. BASE PIN 1. ANODE PIN 1. ANODE 1 PIN 1. SOURCE 1 PIN 1. CATHODE 2. EMITTER 2. EMITTER 2. N/C 2. DRAIN 1/2 2. COMMON ANODE 3. BASE 3. BASE 3. ANODE 2 3. SOURCE 1 3. CATHODE 2 4. COLLECTOR 4. COLLECTOR 4. CATHODE 2 4. GATE 1 4. CATHODE 3 5. COLLECTOR 5. CATHODE 5. CATHODE 1 5. GATE 2 5. CATHODE 4 STYLE 6: STYLE 7: STYLE 8: STYLE 9: Note: Please refer to datasheet for style callout. If style type is not callout. COLLECTOR 3. EMITTER 1 3. BASE 3. N/C 3. ANODE 2 CATHODE 4. COLLECTOR 4. COLLECTOR 4. BASE 4. ANODE 3 out in the datasheet refer to the callout. If style type is not callout. If style type is not callout. If style type is not callout. COLLECTOR 4. COLLECTOR 4. COLLECTOR 5. EMITTER 5. ANODE out in the datasheet refer to the callout. If style type is not callout. If style type is not callout. COLLECTOR 5. COLLECTOR 2/BASE 1 5. COLLECTOR 5. EMITTER 5. ANODE out in the datasheet refer to the callout. If style type is not callout. If style type is not callout. If style type is not call	DESCRIPTION:	SC-88A (SC-70-	5/SOT-353)			PAGE 1 OF 1
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STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5:	PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR	PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR	PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2	PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1	PIN 1. CATHODE 2. COMMON ANOU 3. CATHODE 2 4. CATHODE 3	DE

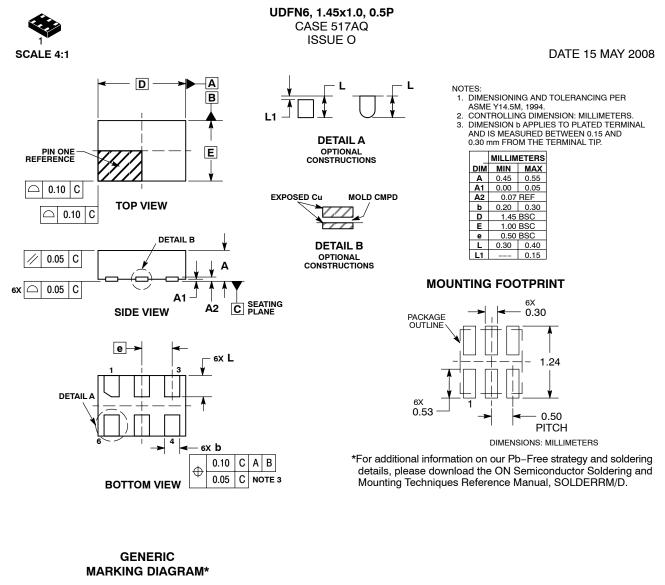
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XXX = Specific Device Code

M = Date Code = Pb-Free Package

⁽Note: Microdot may be in either location)

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- X = Specific Device Code
- M = Date Code
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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PAGE 1 OF 1							
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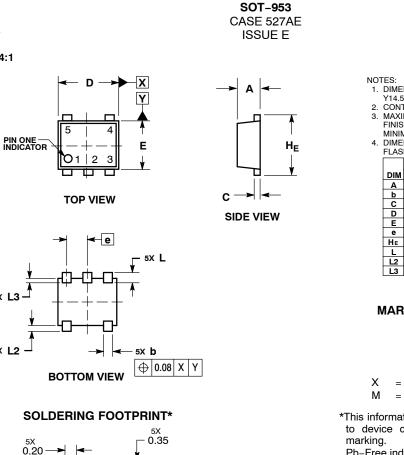
5X L3

5X L2

PACKAGE OUTLINE

0.35 PITCH





DATE 02 AUG 2011

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	, ,						
	MILLIMETERS						
DIM	MIN	NOM	MAX				
Α	0.34	0.37	0.40				
b	0.10	0.10 0.15 0.20					
С	0.07	0.07 0.12 0.17					
D	0.95	0.95 1.00 1.05					
E	0.75	0.80	0.85				
е		0.35 BS	С				
ΗE	0.95	1.00	1.05				
L	0.175 REF						
L2	0.05	0.10	0.15				
L3			0.15				

GENERIC **MARKING DIAGRAM***

= Specific Device Code

= Month Code

*This information is generic. Please refer to device data sheet for actual part

Pb-Free indicator, "G" or microdot " .", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DIMENSIONS: MILLIMETERS

1.20

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